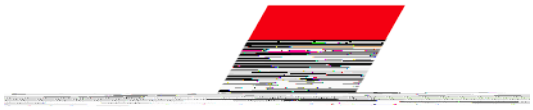

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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

April 2017

FNA51060T3

Motion SPM® 55 Series

Features

- UL Certified No. E209204 (UL1557)
- 600 V - 10 A 3-Phase IGBT Inverter Including Control IC for Gate Drive and Protections
- Low-Loss, Short-Circuit Rated IGBTs
- Separate Open-Emitter Pins from Low-Side IGBTs for Three-Phase Current Sensing
- Active-HIGH interface, works with 3.3 / 5 V Logic, Schmitt-trigger Input
- HVIC for Gate Driving, Under-Voltage and Short-Circuit Current Protection
- Fault Output for Under-Voltage and Short-Circuit Current Protection
- Inter-Lock Function to Prevent Short-Circuit
- Shut-Down Input
- HVIC Temperature-Sensing Built-In for Temperature Monitoring
- Optimized for 5 kHz Switching Frequency
- Isolation Rating: 1500 V_{rms} / min.

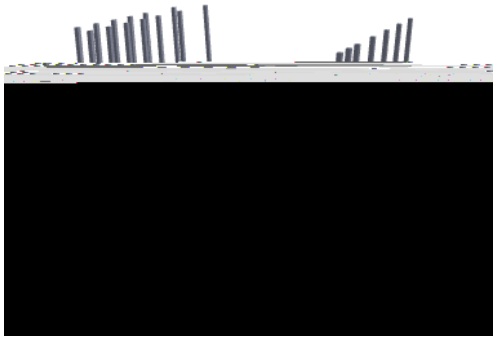
Applications

- Motion Control - Home Appliance / Industrial Motor

Related Resources

General Description

FNA51060T3 is a Motion SPM 55 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC, and PMSM motors. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts, inter-lock function, over-current shutdown, thermal monitoring of drive IC, and fault reporting. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate



Integrated Power Functions

- 600 V - 10 A IGBT inverter for three phase DC / AC power conversion (Please refer to Figure 3)

Integrated Drive, Protection and System Control Functions

- For inverter high-side IGBTs: gate drive circuit, high-voltage isolated high-speed level shifting
  control circuit Under-Voltage Lock-Out (UVLO) protection
- For inverter low-side IGBTs: gate drive circuit, Short-Circuit Protection (SCP)
  control supply circuit Under-Voltage Lock-Out (UVLO) protection
- Fault signaling: corresponding to UVLO (low-side supply) and SC faults
- Input interface: High-active interface, works with 3.3 / 5 V logic, Schmitt trigger input

Pin Configuration

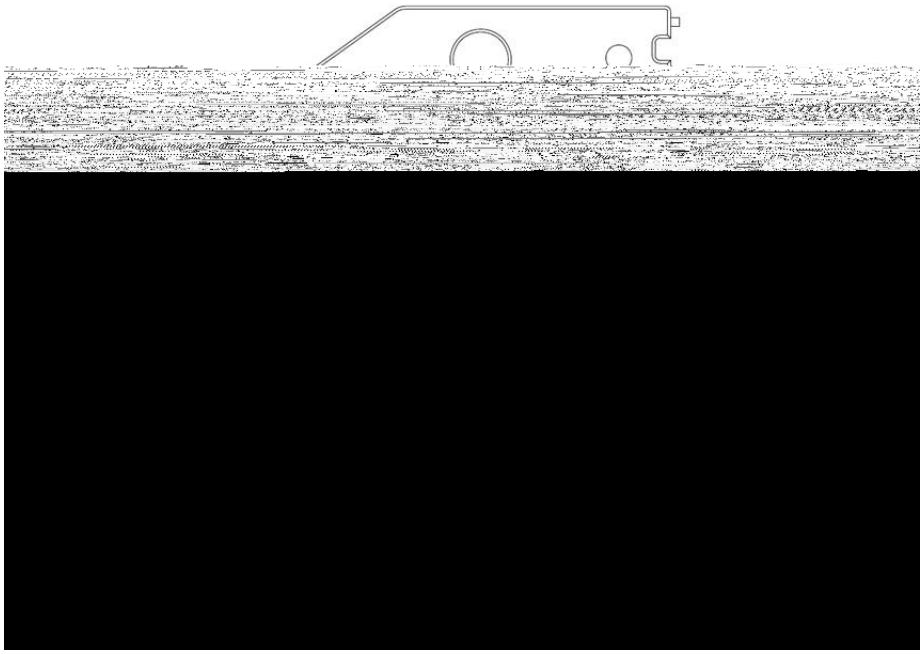


Figure 2. Top View

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	P	Positive DC-Link Input
2	U, $V_S(U)$	Output for U Phase
3	V, $V_S(V)$	Output for V Phase
4	W, $V_S(W)$	Output for W Phase
5	N_U	Negative DC-Link Input for U Phase
6	N_V	Negative DC-Link Input for V Phase
7	N_W	Negative DC-Link Input for W Phase
8	$IN_{(UL)}$	Signal Input for Low-Side U Phase
9	$IN_{(UH)}$	Signal Input for High- ide U Phase
10	$IN_{(VL)}$	Signal Input for Low-Side V Phase
11	$IN_{(VH)}$	Signal Input for High-Side V Phase
12	$IN_{(WL)}$	Signal Input for Low-Side W Phase
13	$IN_{(WH)}$	Signal Input for High-Side W Phase
14	V_{DD}	Common Bias Voltage for IC and IGBTs Driving
15	COM	Common Supply Ground
16	C_{SC}	Capacitor (Low-Pass Filter) for Short-circuit Current Detection Input
17	V_F	Fault Output, Shut-Down Input, Temperature Output of Drive IC
18	$V_{B(W)}$	High-Side Bias Voltage for W-Phase IGBT Driving
19	$V_{B(V)}$	High-Side Bias Voltage for V-Phase IGBT Driving
20	$V_{B(U)}$	High-Side Bias Voltage for U-Phase IGBT Driving

Internal Equivalent Circuit and Input/Output Pins

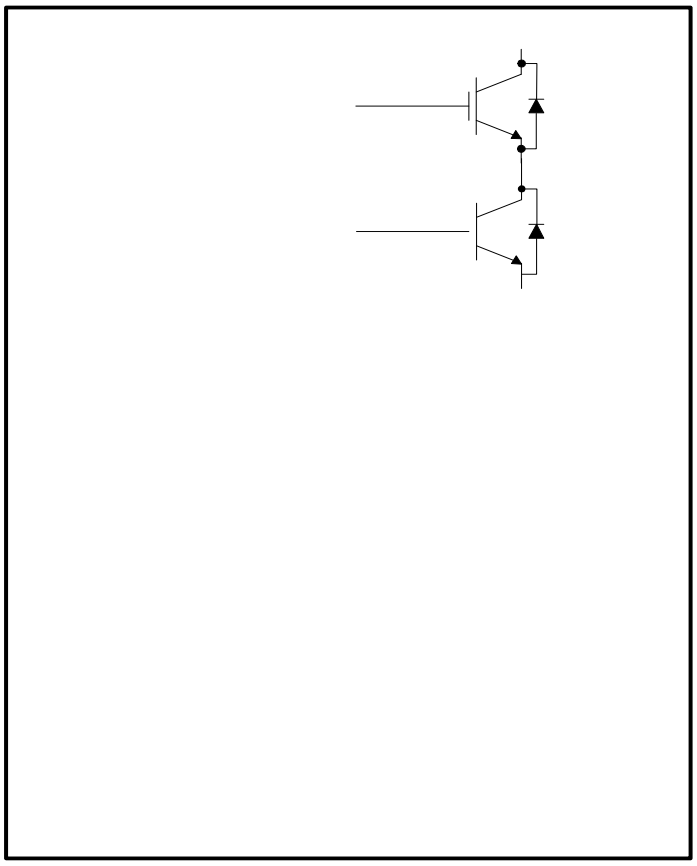


Figure 3. Internal Block Diagram

Note:

1. Inverter high-side is composed of three IGBTs, freewheeling diodes, and one control IC for each IGBT.
2. Inverter low-side is composed of three IGBTs, freewheeling diodes, and one control IC for each IGBT. It has gate drive and protection functions.
3. Single drive IC has gate driver for six IGBTs and protection functions.
4. Inverter power side is composed of four inverter DC-link input terminals and three inverter output terminals.

Absolute Maximum Ratings (T_J = 25°C, unless otherwise specified.)

Inverter Part

Note:

5. The maximum junction temperature rating of the power chips integrated within the Motion SPM® 55 product is 150°C.

Control Part

Total System

Thermal Resistance

Note:

Electrical Characteristics (T_J = 25°C, unless otherwise specified.)

Inverter Part

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{CE(SAT)}$	Collector - Emitter Saturation Voltage	$V_{DD} = V_{BS}$ = 15 V V_{IN} = 5 V I_C = 10 A				

Note:

7. t_{ON} and t_{OFF} include the propagation delay of the internal drive IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

Figure 4. Switching Time Definition

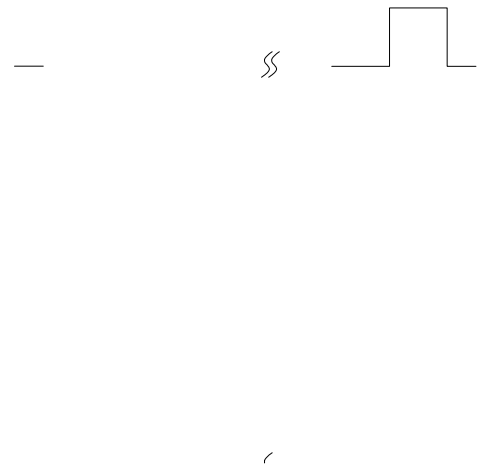
Control Part

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
I_{QDD}	Quiescent V_{DD} Supply Current	V_{DD} = 15 V, $IN_{(UH,VH,WH,UL,VL,WL)}$ = 0 V	V_{DD} - COM	-	2.3	3.4	mA
I_{PDD}	Operating V_{DD} Supply Current	V_{DD} = 15 V, f_{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input	V_{DD} - COM	-	2.7	4.0	mA
I_{QBS}	Quiescent V_{BS} Supply Current	V_{BS} = 15 V, $IN_{(UH, VH, WH)}$ = 0 V	$V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	-	60	100	μA
I_{PBS}	Operating V_{BS} Supply Current	V_{DD} = V_{BS} = 15 V, f_{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input for high - side	$V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$duty = 5				

Note:

8. Short-circuit protection is functioning for all six IGBTs.

Figure. 5. V-T Curve of Temperature Output of IC (5V pull-up with 4.7kohm)



(with the external shunt resistance and CR connection)

c1 : Normal operation: IGBT ON and carrying current.

c2 : Short circuit current detection (SC trigger).

c3 : Hard IGBT gate interrupt.

c4 : IGBT turns OFF.

c5 : Input “L” : IGBT OFF state.

c6 : Input “H”: IGBT ON state, but during the active period of fault output the IGBT doesn’t turn ON.

c7 : IGBT OFF state

Figure 11. Short-Circuit Protection

d1 : High Side First - Input - First - Output Mode

d2 : Low Side Noise Mode : No Lo

d3 : High Side Noise Mode : No Ho

d4 : Low Side First - Input - First - Output Mode

d5 : In - Phase Mode : No Ho

Figure 12. Inter-Lock Function

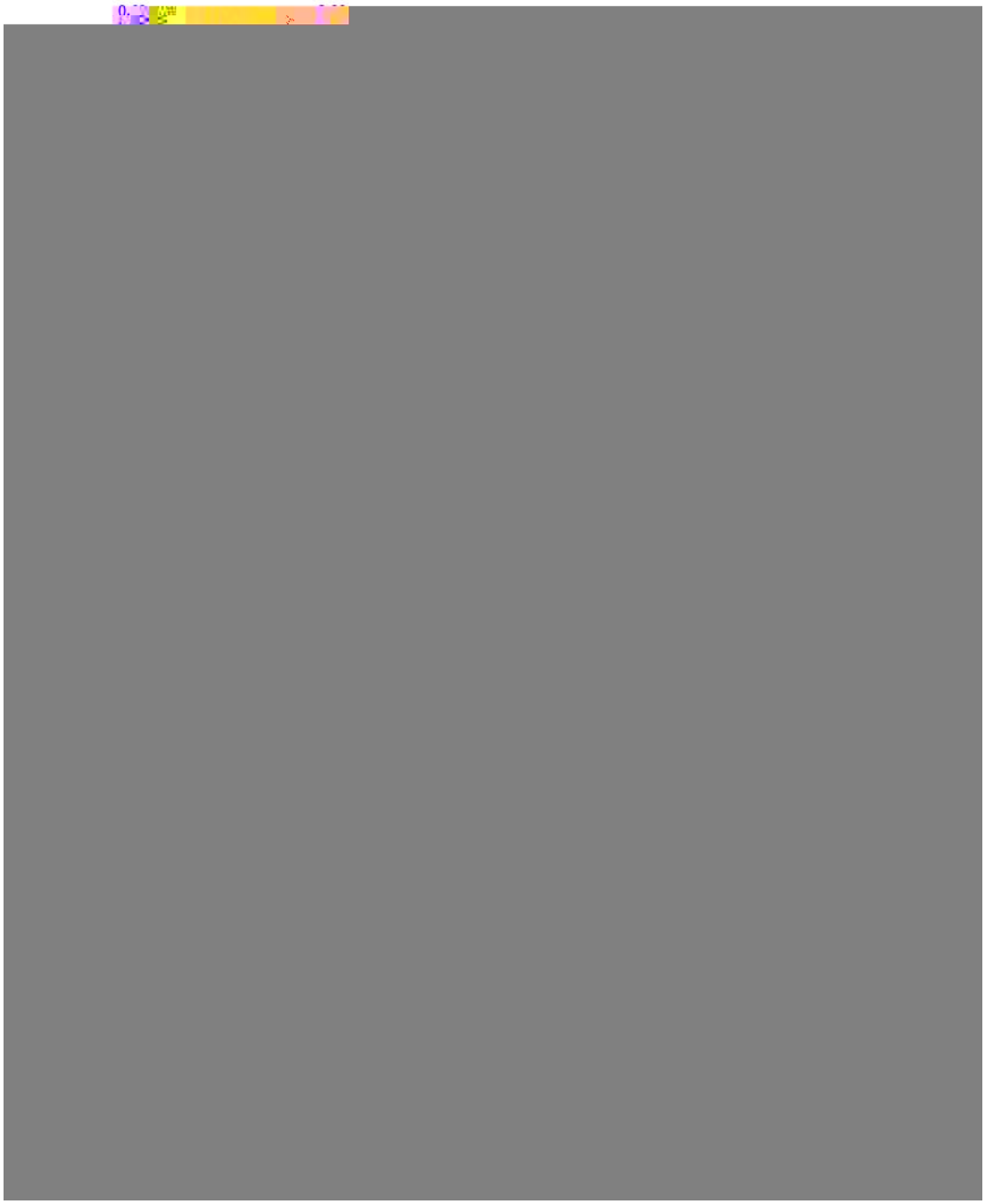
Note:

1) To avoid malfunction, the wiring of each input should be as short as possible. (less than 2 ~ 3 cm)

2) By virtue of integrating an application specific type of HVIC inside the SPM® 55 product, direct coupling to MCU terminals without any opto-coupler or transformer isolation is possible.

3) V

Detailed Package Outline Drawings (FNA51060T3, Long Lead)



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